# NST856BF3T5G

# PNP General Purpose Transistor

The NST856BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### **Features**

- h<sub>FE</sub>, 220-475
- Low  $V_{CE(sat)}$ ,  $\leq -0.3 \text{ V}$
- Reduces Board Space
- This is a Halide-Free Device
- This is a Pb-Free Device

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-65	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	-100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 1)	432	°C/W
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R <sub>ΨJL</sub> (Note 2)	143	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

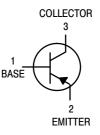
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 100 mm<sup>2</sup> 1 oz, copper traces.
- 2. 500 mm<sup>2</sup> 1 oz, copper traces.



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NST856BF3T5G



SOT-1123 CASE 524AA STYLE 1

## **MARKING DIAGRAM**



A = Device Code M = Date Code

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NST856BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## NST856BF3T5G

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA)	V <sub>(BR)CEO</sub>	-65	-	-	V
Collector - Emitter Breakdown Voltage (I <sub>C</sub> = -10 μA, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	-80	-	-	V
Collector – Base Breakdown Voltage (I <sub>C</sub> = -10 μA)	V <sub>(BR)CBO</sub>	-80	-	-	V
Emitter – Base Breakdown Voltage ( $I_E = -1.0 \mu A$ )	V <sub>(BR)EBO</sub>	-5.0	-	-	V
Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ ) ( $V_{CB} = -30 \text{ V}$ , $T_A = 150 ^{\circ}\text{C}$ )	I <sub>CBO</sub>	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C = -10~\mu\text{A},~V_{CE} = -5.0~\text{V})\\ &(I_C = -2.0~\text{mA},~V_{CE} = -5.0~\text{V}) \end{aligned} $	h <sub>FE</sub>	- 220	150 290	- 475	-
Collector – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>CE(sat)</sub>	- -	- -	-0.3 -0.8	V
Base – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>BE(sat)</sub>	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage ( $I_C$ = -2.0 mA, $V_{CE}$ = -5.0 V) ( $I_C$ = -10 mA, $V_{CE}$ = -5.0 V)	V <sub>BE(on)</sub>	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ( $I_C = -10$ mA, $V_{CE} = -5.0$ Vdc, $f = 100$ MHz)	f <sub>T</sub>	100	_	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	-	4.5	pF
Input Capacitance ( $V_{EB} = -0.5 \text{ V}, I_C = 0 \text{ mA}, f = 1.0 \text{ MHz}$ )	C <sub>ibo</sub>	-	_	10	pF
Noise Figure (I <sub>C</sub> = -0.2 mA, V <sub>CE</sub> = -5.0 Vdc, R <sub>S</sub> = 2.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	_	_	10	dB

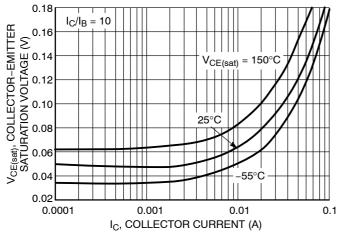


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

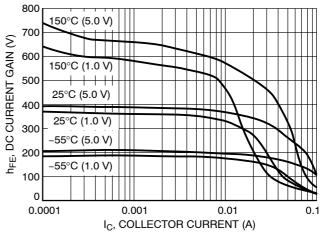


Figure 2. DC Current Gain vs. Collector Current

## NST856BF3T5G

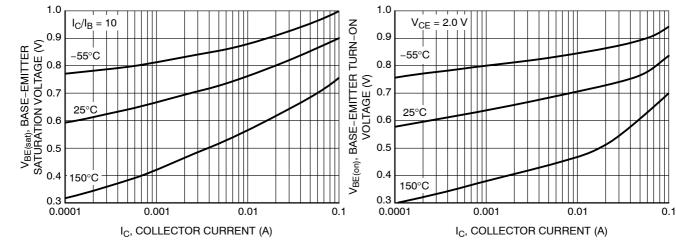


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Turn-On Voltage vs.
Collector Current

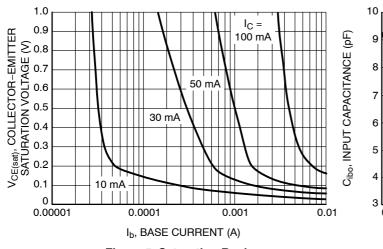


Figure 5. Saturation Region

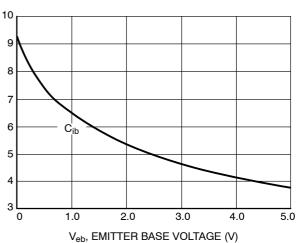


Figure 6. Input Capacitance

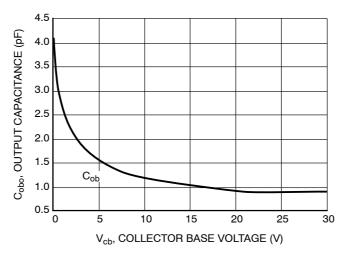


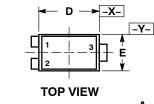
Figure 7. Output Capacitance

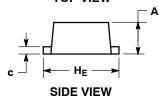


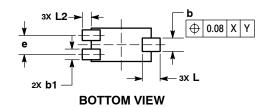
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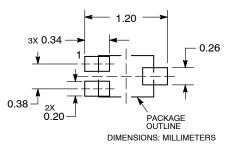
#### SCALE 8:1







#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.34	0.40		
b	0.15	0.28		
b1	0.10	0.20		
С	0.07	0.17		
D	0.75	0.85		
E	0.55	0.65		
е	0.35	0.40		
HE	0.95	1.05		
L	0.185 REF			
L2	0.05	0.15		

### **GENERIC MARKING DIAGRAM\***



= Specific Device Code Χ Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part

marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURC
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

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DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P		PAGE 1 OF 1	

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